

#### **Features**

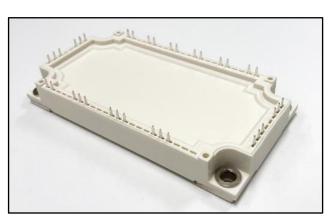
- Low V<sub>CE(sat)</sub>
- Fast Switching
- High Ruggedness
- Short-Circuit Rated



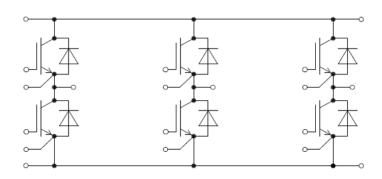
Product Summary				
V <sub>CES</sub>	1200V			
Ic	150A			
V <sub>CE(sat),typ</sub>	1.6V			

### **Applications**

- General Purpose Inverters
- Frequency Converters
- Industrial Motor Drives
- Uninterruptible Power Supply (UPS)
- Servos



#### **Internal Connection**





## IGBT, Inverter

#### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Collector-to-Emitter Voltage	V <sub>CES</sub>	1200	
Gate-to-Emitter Voltage	.,	±20	V
Transient Gate-emitter Voltage ( $t_p \le 10\mu s$ , D < 0.010)	.010) VGES		
Continuous DC Collector Current (T <sub>C</sub> = 100 °C, T <sub>J</sub> = 175 °C)	Icdc	150	
Repetitive Peak Collector Current (tp = 1ms)	ICRM	300	A
Maximum Power Dissipation (T <sub>C</sub> = 25°C, T <sub>J</sub> = 175°C)	P <sub>D(max)</sub>	735	W



### Electrical Characteristics (1), (2)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-to-Emitter Breakdown Voltage	BV <sub>CES</sub>	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA	1200	-	-	V
Collector-to-Emitter Leakage Current	Ices	V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0V	-	-	5	mA
Gate-to-Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> = 0V, V <sub>GE</sub> = ±20V	-	-	400	nA
Gate Threshold Voltage	V <sub>GE(th)</sub>	$V_{CE} = V_{GE}$ , $I_C = 1.5 \text{mA}$	4.8	6	7.2	
		V <sub>GE</sub> = 15V, I <sub>C</sub> = 150A	-	1.6	2.0	
		V <sub>GE</sub> = 15V, I <sub>C</sub> = 150A,		4.05		V
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	T <sub>J</sub> = 150°C	-	1.95	-	
		V <sub>GE</sub> = 15V, I <sub>C</sub> =150A, T <sub>J</sub> =175°C	-	2.05	-	
Total Gate Charge	Qg	$V_{CC} = 600V,$ $V_{GE} = \pm 15V,$ $I_{C} = 150A$	-	1.44	-	μС
Internal Gate Resistance	RGint	-	-	3	-	Ω
Input Capacitance	Ciss	V <sub>CE</sub> = 25V,	-	9.73	-	
Output Capacitance	Coss	V <sub>GE</sub> = 0V,	-	0.68	-	nF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1MHz	-	0.13	-	
Turn-on Delay time	t <sub>d(ON)</sub>		-	358	-	ns mJ
Rise Time	tr	V <sub>CC</sub> = 600V,	-	48	-	
Turn-off Delay time	t <sub>d(OFF)</sub>	$V_{GE} = \pm 15V$ , $R_G = 5.1\Omega$ ,	-	452	-	
Fall Time	t <sub>f</sub>	$I_{C} = 150A,$ $L_{load} = 0.82mH,$	-	154	-	
Turn-On Switching Loss	Eon	Energy losses include "tail" and diode reverse	-	8.5	-	
Turn-Off Switching Loss	E <sub>off</sub>	recovery.	-	10.0	-	
IGBT Total Switching Loss	Ets		-	18.5	-	
Turn-on Delay time	t <sub>d(ON)</sub>		-	632	-	
Rise Time	tr	$V_{CC} = 600V$ , $V_{GE} = \pm 15V$ ,	-	60	-	
Turn-off Delay time	t <sub>d(OFF)</sub>	$R_G = 5.1\Omega$ , $I_C = 150A$ ,	-	470	-	ns
Fall Time	t <sub>f</sub>	L <sub>load</sub> = 0.82mH,	-	278	-	
Turn-On Switching Loss	Eon	Energy losses include "tail" and diode reverse	-	14.2	-	
Turn-Off Switching Loss	E <sub>off</sub>	recovery. T <sub>J</sub> = 150°C	-	16.8	-	mJ
IGBT Total Switching Loss	Ets	.,_ 150 C	-	31	-	
Short Circuit Collector Current	Ic(sc)	$V_{GE}$ = 15V, $V_{CC} \le 600V$ , $tsc \le 10\mu s$	-	600	-	А



# Diode, Inverter

### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	1200	V
Continuous DC Forward Current	l <sub>F</sub>	150	^
Repetitive Peak Forward Current (tp = 1ms)	IFRM	300	А

#### **Electrical Characteristics** (1)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Diode Forward Voltage		I <sub>F</sub> = 150A	-	2.0	2.4	V	
	VF	I <sub>F</sub> = 150A T <sub>J</sub> = 150°C	-	1.8	-		
		I <sub>F</sub> = 150A T <sub>J</sub> = 175°C	-	1.75	-		
Diode Reverse-Recovery Charge	Qrr		-	10.66	-	μC	
Diode Peak Reverse-Recovery Current	Irrm	V <sub>R</sub> = 600V, I <sub>F</sub> = 150A, dI <sub>F</sub> /dt = -1690 A/μs	-	99	-	Α	
Diode Reverse-Recovery Loss	Err	•	-	3.35	-	mJ	

# • NTC thermistors

#### **Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Rated Resistance	R <sub>25</sub>	-	-	5.0	-	kΩ
Deviation of R100	ΔR/R	$T_{C} = 100^{\circ}C$ $R_{100} = 493\Omega$	-5	-	5	%
Power Dissipation	P <sub>25</sub>	-	-	-	20.0	mW
B-value	B <sub>25/50</sub>	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 K))]$	-	3375	-	К

## Module

### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Maximum Junction Temperature	Tj	-40 to +175	
Operating Junction Temperature	T <sub>vj op</sub>	-40 to +150	°C
Storage Temperature	Tstg	-40 to +125	
Isolation Voltage (RMS, f = 50 Hz, t = 1 min)	Viso	2.5	kV



#### **Characteristics**

Parameter	Symbol	Min	Тур	Max	Unit
Material of Module Baseplate	-	-	Cu	-	-
Internal Isolation	-	-	Al <sub>2</sub> O <sub>3</sub>	-	-
Creepage Distance, Terminal to Terminal	-	-	10	-	mm
Clearance, Terminal to Terminal	-	-	7.5	-	mm
Stray Inductance, Module	LSCE	-	21	-	nH
Module Lead Resistance, Terminal to Chip	R <sub>CC'+EE'</sub>	-	1.8	-	mΩ
Junction-to-Case Thermal Resistance, per IGBT, Inverter		-	0.17	-	°C /\\
Junction-to-Case Thermal Resistance, per Diode, Inverter	Rөлс	-	0.26	-	°C/W
Case-to-Heatsink Thermal Resistance, per IGBT, Inverter		-	0.09	-	
Case-to-Heatsink Thermal Resistance, per Diode, Inverter	R <sub>ӨСН</sub>	-	0.16	-	°C/W
Case-to-Heatsink Thermal Resistance, per Module		-	0.01	-	
Mounting Torque for Module Mounting, Screw M5	М	3.0	-	6.0	Nm
Weight per Module	G	-	300	-	g

(1)  $T_J = 25$ °C unless otherwise specified

(2)  $t_r$ : from 10% of lc to 90% of lc;  $t_f$ : from 90% of lc to 10% of lc;

 $E_{on} :$  from 10% of  $V_{GE}$  to 10% of  $V_{CE}; \quad E_{off} :$  from 90% of  $V_{GE}$  to 10% of  $I_C.$ 



# • Typical Electrical Characteristics

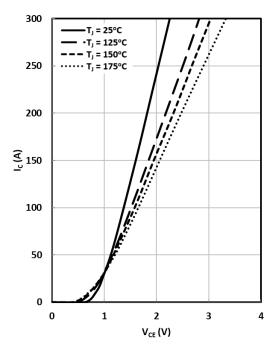
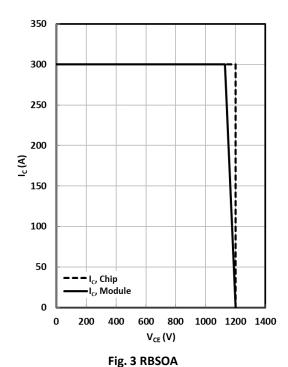


Fig. 1 IGBT (Inverter) Output Characteristics



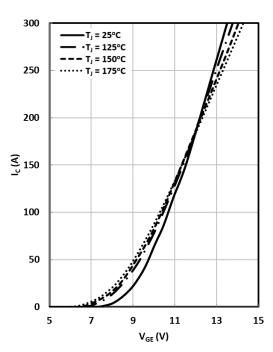


Fig. 2 IGBT (Inverter) Transfer Characteristics

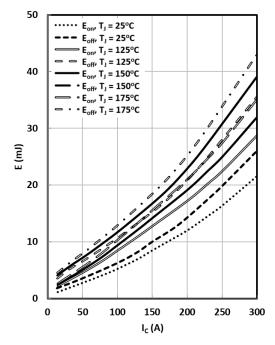


Fig. 4 IGBT Switching Loss VS.  $I_C$ ( $V_{CC}$  = 600V,  $V_{GE}$  = ±15V,  $R_G$  = 5.1 $\Omega$ )



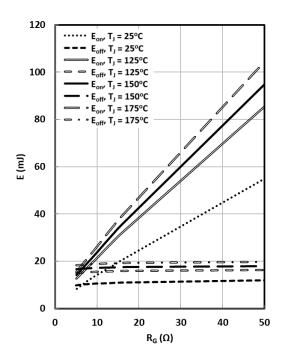


Fig. 5 IGBT Switching Loss VS.  $R_G$ ( $V_{CC}$  = 600V,  $V_{GE}$  = ±15V,  $I_C$  = 150A)

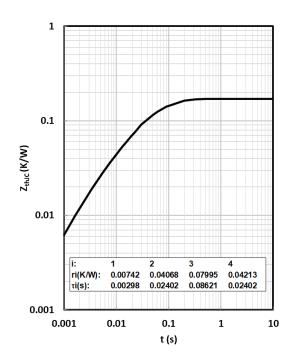


Fig. 6 IGBT (Inverter) Transient Thermal Impedance

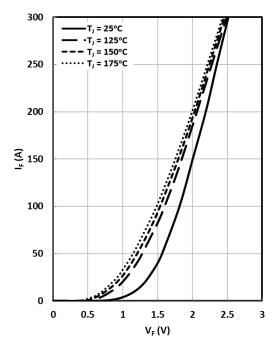


Fig. 7 Diode (Inverter) Forward Characteristics

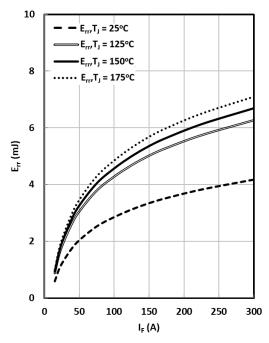


Fig. 8 Diode (Inverter) Switching Loss vs.  $I_F$  ( $V_{CC}$  = 600V,  $R_G$  = 5.1 $\Omega$ )



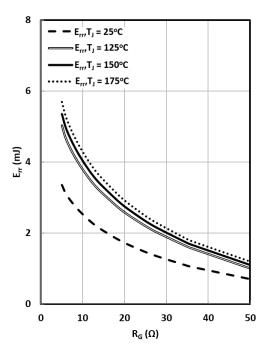


Fig. 9 Diode (Inverter) Switching Loss vs.  $R_G$  ( $V_{CC}$  = 600V,  $I_F$  = 150A)

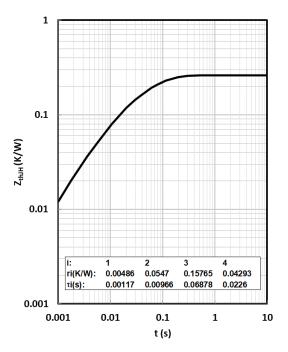


Fig. 10 Diode (Inverter) Transient Thermal Impedance

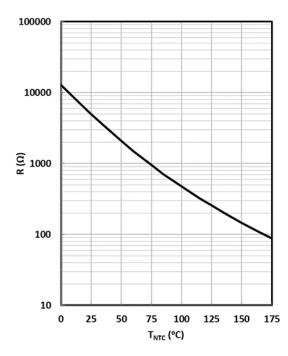
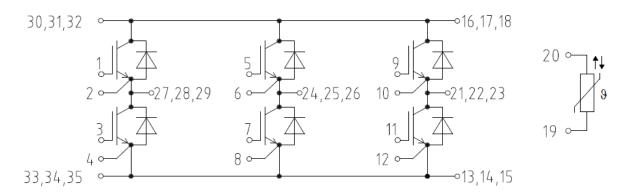


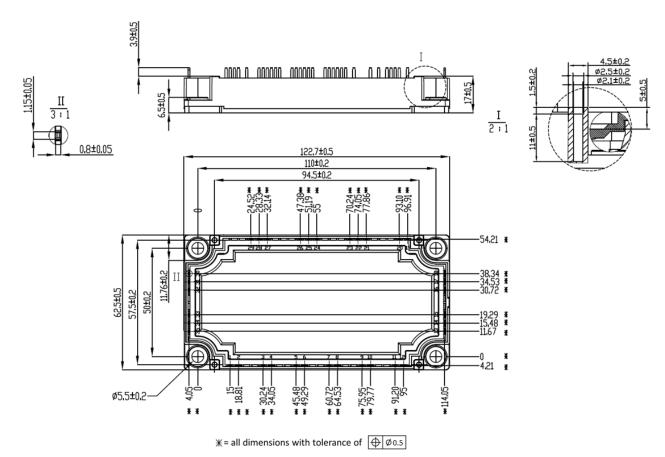
Fig. 11 NTC Temperature Characteristics



# • Circuit diagram



# • Package Dimensions





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